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**INFORMATION DISCLOSURE  
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Sheet 1 of 2

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Complete if Known

Application Number 10/602315

Filing Date June 24, 2003

First Named Inventor Ahn, Kie

Group Art Unit 2812 2829

Examiner Name Unknown

Attorney Docket No: 1303.107US1

**US PATENT DOCUMENTS**

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T*
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		KUKLI, K, et al., "Comparison of hafnium oxide films grown by atomic layer deposition from iodide and chloride precursors", <u>Thin Solid Films</u> , 416, (2002),72-79	
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		KUKLI, K J., et al., "Properties of hafnium oxide films grown by atomic layer deposition from hafnium tetraiodide and oxygen", <u>Journal of Applied Physics</u> , 92(10), (November 15, 2002),5698-5703	
		LEE, BYOUNG H., et al., "Characteristics of TaN gate MOSFET with ultrathin hafnium oxide (8 A-12 A)", <u>Electron Devices Meeting, 2000. IEDM Technical Digest. International</u> , (2000),39-42	
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Asok Kumar Sarkar

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